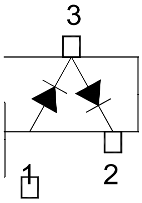
SOT-23

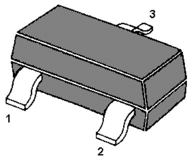
MMBD172SE

www.china-base.com.hk

SILICON EPITAXIAL PLANAR DIODE

for VHF~UHF band RF attenuator applications





Marking Code: **FP**
SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	50	V
Forward Current	I_F	50	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_s	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at I_F = 10 mA	V_F	-	-	1	V
Reverse Voltage at I_R = 10 µA	V_R	50	-	-	V
Reverse Current at V_R = 50 V	I_R	-	-	0.1	µA
Total Capacitance at V_R = 50 V, f = 1 MHz	C_T	-	0.25	-	pF
Series Resistance [1] at I_F = 10 mA, f = 100 MHz	r_s	-	7	-	Ω

[1] C_T is measured by 3 terminal method with capacitance bridge.